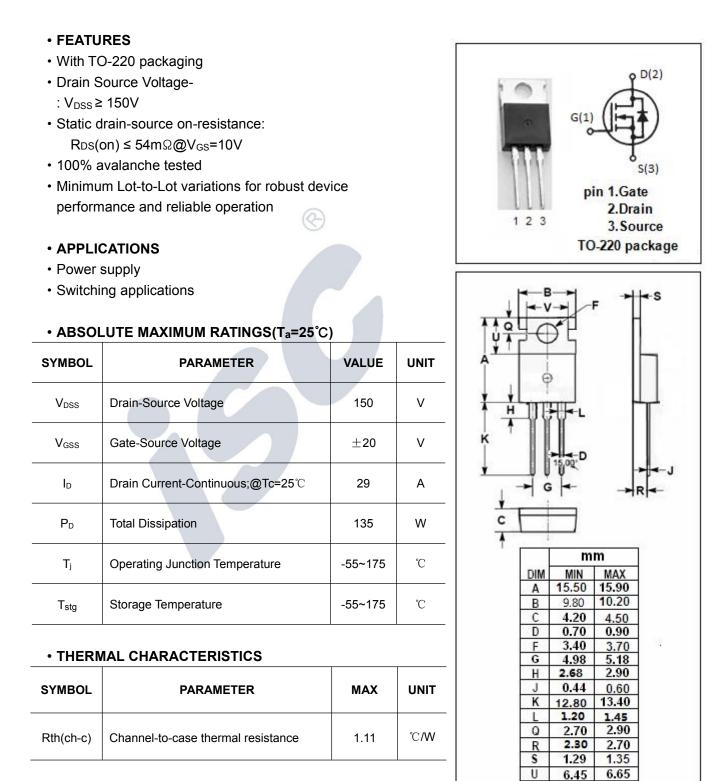


### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

### FDP2572



isc website: www.iscsemi.cn

isc & iscsemi is registered trademark

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8.66

8.86

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## isc N-Channel MOSFET Transistor

### FDP2572

#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 250uA	150			V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =250uA	2		4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 9A			54	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V;V <sub>DS</sub> = 0V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 120V; V <sub>GS</sub> = 0V V <sub>DS</sub> = 120V; V <sub>GS</sub> = 0V;T <sub>J</sub> =150°C			1 250	μA
VSDF	Diode forward voltage	I <sub>SD</sub> = 9A, V <sub>GS</sub> = 0 V			1.25	V

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